

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-4 (Canceled)

5. (Currently Amended) A method for producing a silicon wafer having a crystal orientation <110> from a silicon single crystal ingot grown by Floating Zone method (FZ method), wherein, at least, an FZ silicon single crystal ingot is grown by being made to be dislocation-free by Dash Necking method using a seed crystal having its crystal axis inclined at a specified angle from a crystal orientation <110>, and the grown FZ silicon single crystal ingot is sliced at the just angle of a crystal orientation <110> to produce a silicon wafer having a crystal orientation <110>. <110>, and the sliced silicon wafer having a crystal orientation <110> is made to be a perfect circle by processing of chamfering.

6. (Canceled)

7. (Previously Presented) The method for producing a silicon wafer according to Claim 5, wherein the specified angle of inclining the seed crystal is 1° to 30°.

8. (Canceled)

9. (Previously Presented) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 5.

10. (Canceled)

11. (Previously Presented) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 7.

12. (Canceled)